

**Amendments to the Claims**

This listing of claims will replace all prior listings of claims in the application.

**Listing of Claims**

1. (Canceled)

2. (Canceled)

3. (Currently Amended) A method for forming a CVD film according to ~~claim 1~~Claim 7, wherein ~~the inside~~ the process chamber is under an oxygen or nitrogen plasma condition when the process gas is introduced therein.

4. (Currently Amended) A method for forming a CVD film according to ~~claim 1~~Claim 7, wherein ~~the~~a gas plasma is applied continuously on the substrate in the ~~same~~ process chamber after the introduction of the process gas in the process chamber in order to improve the film characteristics.

5. (Currently Amended) A method for forming a CVD film according to ~~claim 1~~Claim 7, wherein ~~the process~~ after the introduction of the process gas, the steps are repeated in ~~the same process chamber in order to~~ obtain a uniform predetermined thickness film.

6. (Canceled)

7. (New) A method of forming a CVD film on a substrate, comprising the steps of:

providing a chemical vapor deposition apparatus comprising a belljar process chamber, an electromagnetic coil for generating a helicon wave in the process chamber provided around an upper portion of the process chamber, nozzles for

supplying a plasma gas provided underneath the electromagnetic coil and around an upper portion of the process chamber, nozzles for supplying a process gas provided equidistantly around the circumference of the process chamber underneath the nozzles for supplying a plasma gas, heating means for heating the substrate, a pressure control gate valve for controlling the pressure in the process chamber, a turbo molecular pump for reducing the pressure in the process chamber and a gate valve for opening the process chamber and allowing handling of the substrate; and

conducting chemical vapor deposition of the film on the substrate in the process chamber under conditions wherein introduction of the process gas into the process chamber and evacuation of the process chamber does not occur simultaneously.

8. (New) A method of forming a CVD film on a substrate, comprising the steps of:

providing a chemical vapor deposition apparatus comprising a belljar process chamber, an electromagnetic coil for generating a helicon wave in the process chamber provided around an upper portion of the process chamber, nozzles for supplying a plasma gas provided underneath the electromagnetic coil and around an upper portion of the process chamber, nozzles for supplying a process gas provided equidistantly around the circumference of the process chamber underneath the nozzles for supplying a plasma gas, heating means for heating the substrate, a pressure control gate valve for controlling the pressure in the process chamber, a turbo molecular pump for reducing the pressure in the process chamber and a gate valve for opening the process chamber and allowing handling of the substrate; and

conducting chemical vapor deposition of the film on the substrate under conditions wherein either introduction of a process gas in a process chamber or oxidizing or nitrifying a

film formed on the substrate and evacuation of the process chamber does not occur simultaneously.

9. (New) A method of forming a CVD film on a substrate, comprising the steps of:

providing a chemical vapor deposition apparatus comprising a belljar process chamber;

introducing the substrate into the process chamber;

providing a vacuum in the process chamber;

closing a pressure control gate valve;

supplying a process gas to the process chamber and commencing deposition of a film onto the substrate;

stopping the supply of the process gas to the process chamber and continuing with the deposition of the film on the substrate;

opening the pressure control gate valve to reduce the pressure in the process chamber;

supplying an oxidizing or nitrifying gas into the process chamber and applying a plasma therein; and

stopping the supply of the oxidizing or nitriding gas and stopping the application of the plasma in the process chamber to form the CVD film on the substrate.

10. (New) A method of forming a CVD film on a substrate, comprising the steps of:

providing a chemical vapor deposition apparatus comprising a belljar process chamber;

introducing the substrate into the process chamber;

providing a vacuum in the process chamber;

closing a pressure control gate valve;

supplying a process gas to the process chamber and commencing the application of a plasma in the process chamber to commence deposition of a film onto the substrate;

stopping the supply of the process gas to the process chamber while still applying a plasma in the process chamber to continue the deposition of the film onto the substrate;

opening the pressure control gate to reduce the pressure in the process chamber;

supplying an oxidizing or nitrifying gas into the process chamber; and

stopping the supply of the oxidizing or nitrifying gas and stopping the application of the plasma in the process chamber to form the CVD film on the substrate.